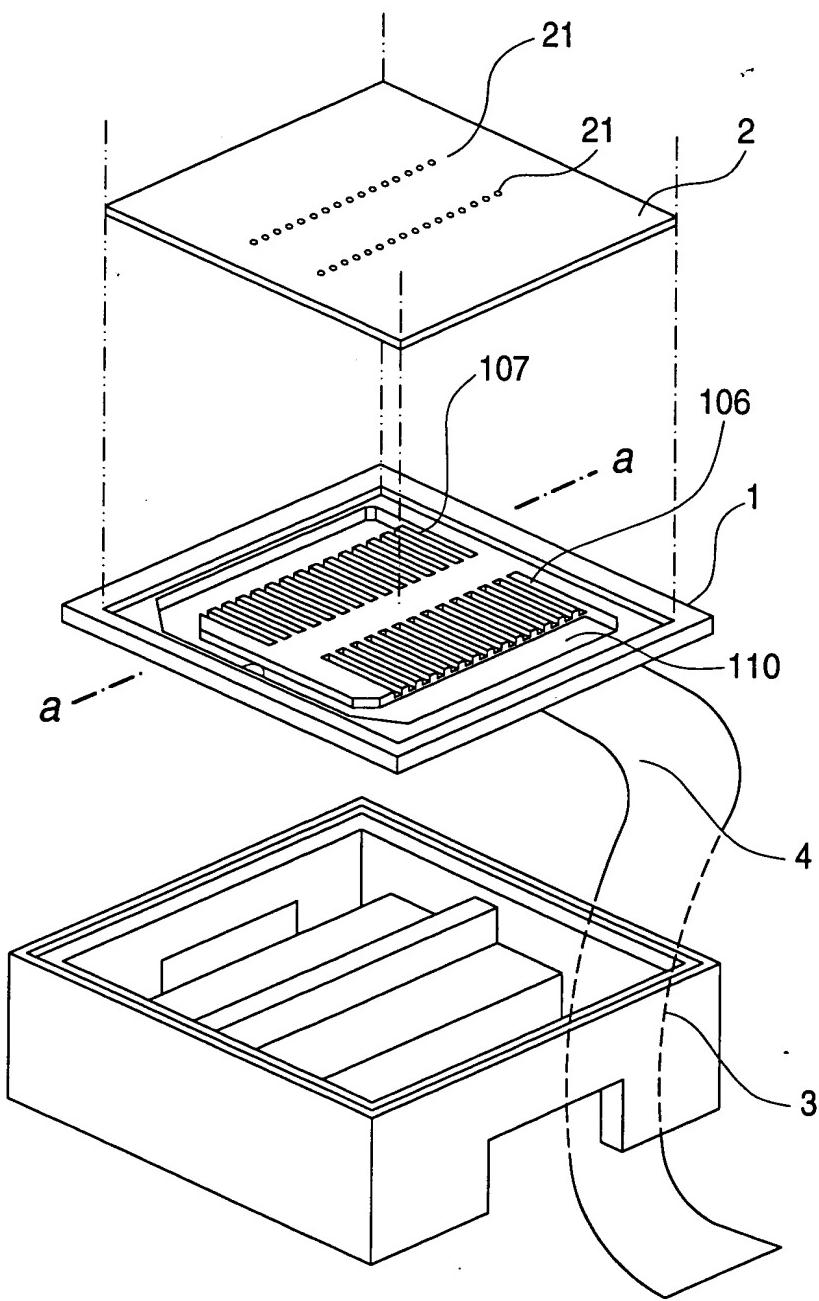


89/599,440

1/17

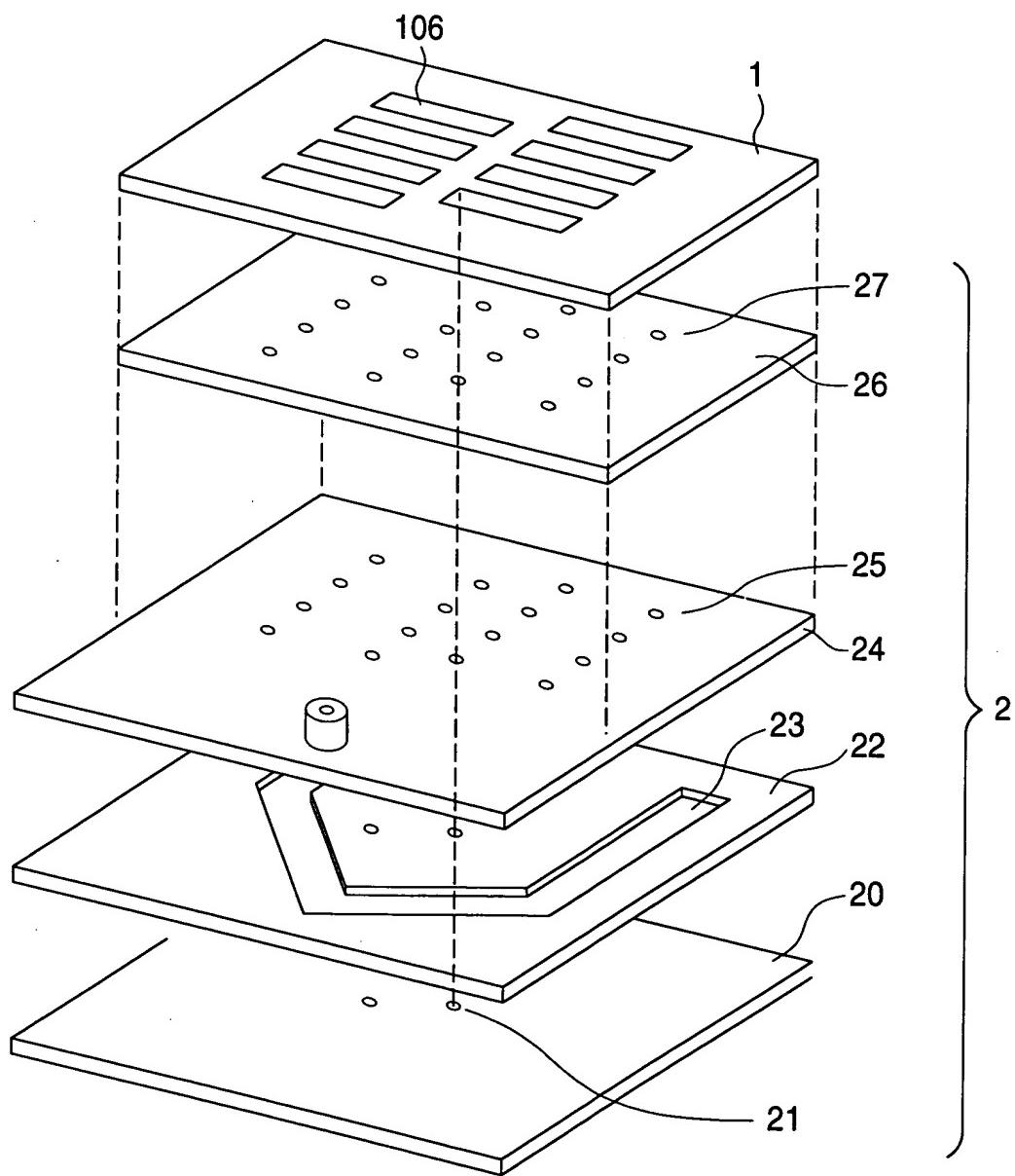
FIG. 1



09/598,840

2/17

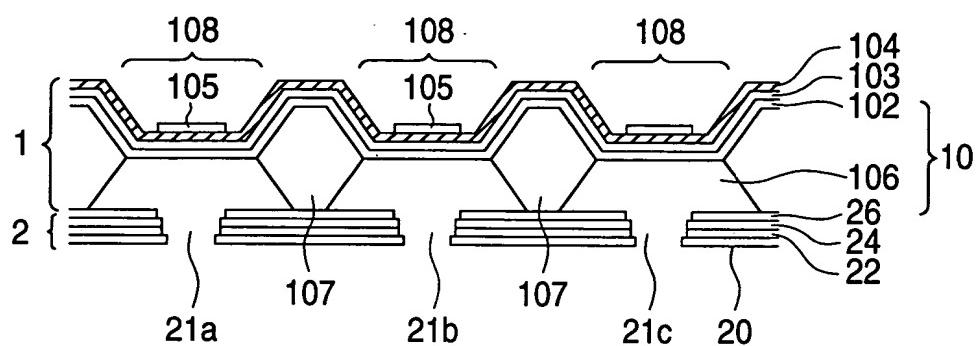
FIG. 2



89/599,440

3/17

FIG. 3



09/15/99, 440

4/17

FIG. 4A

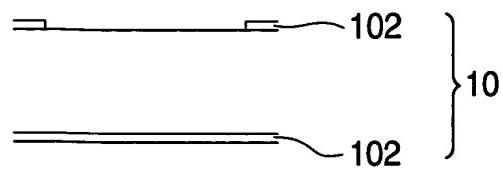


FIG. 4B

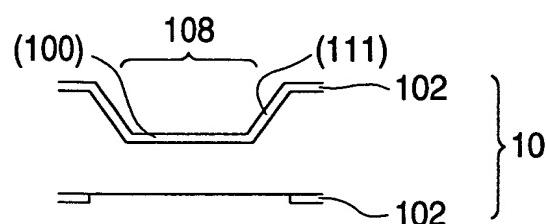


FIG. 4C

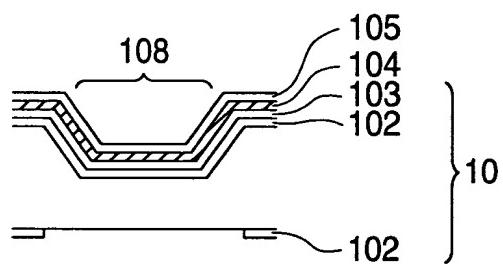


FIG. 4D

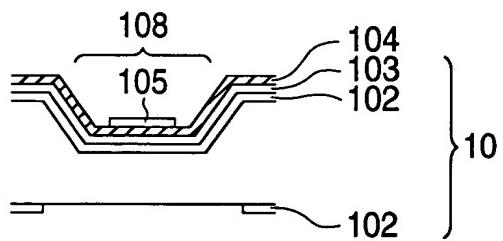
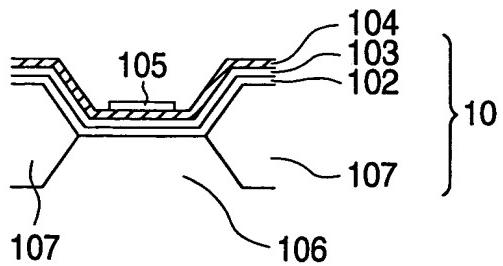


FIG. 4E



69/599,449

5/17

FIG. 5

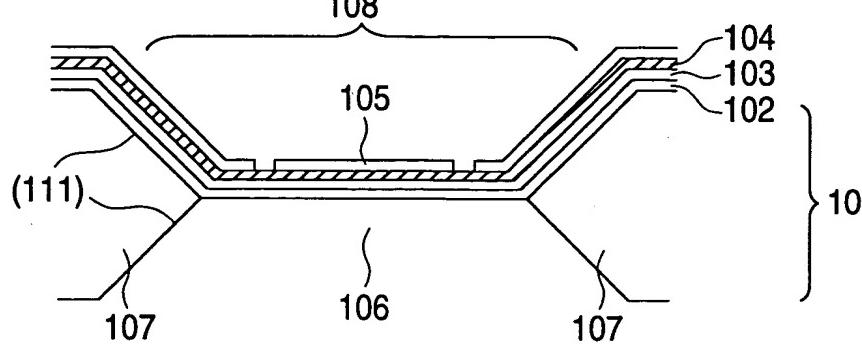


FIG. 6

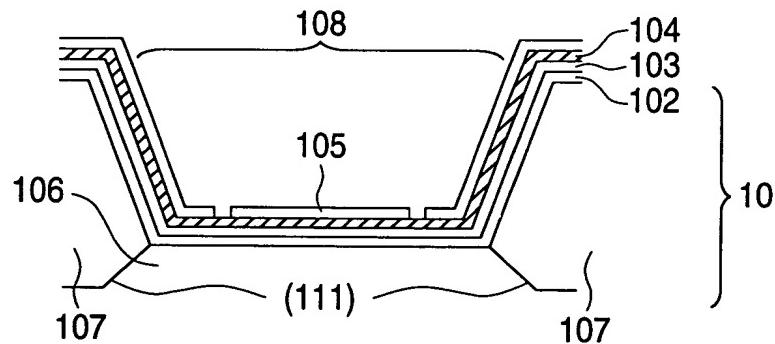
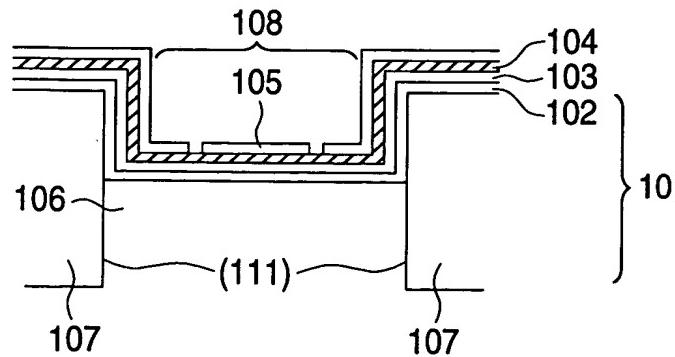


FIG. 7



09/599440

6/17

FIG. 8

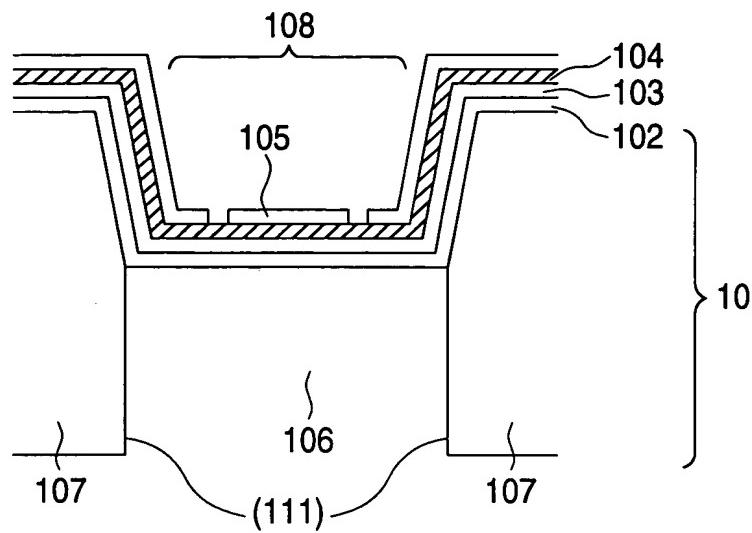
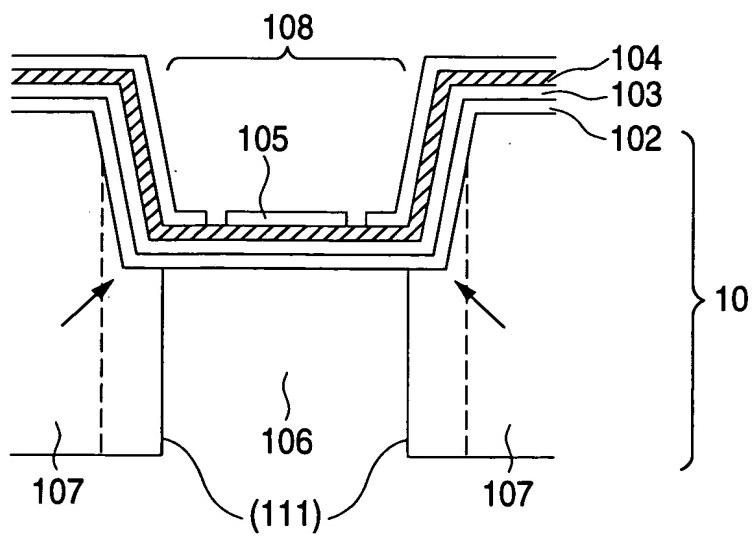


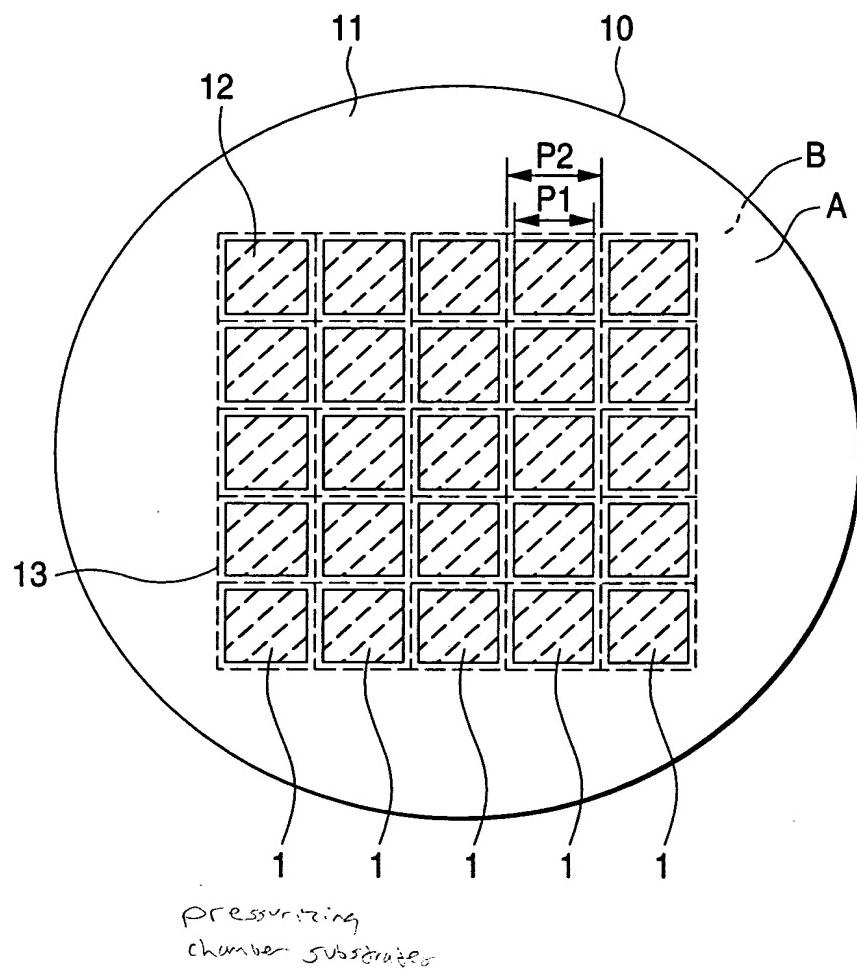
FIG. 9



09/599440

7/17

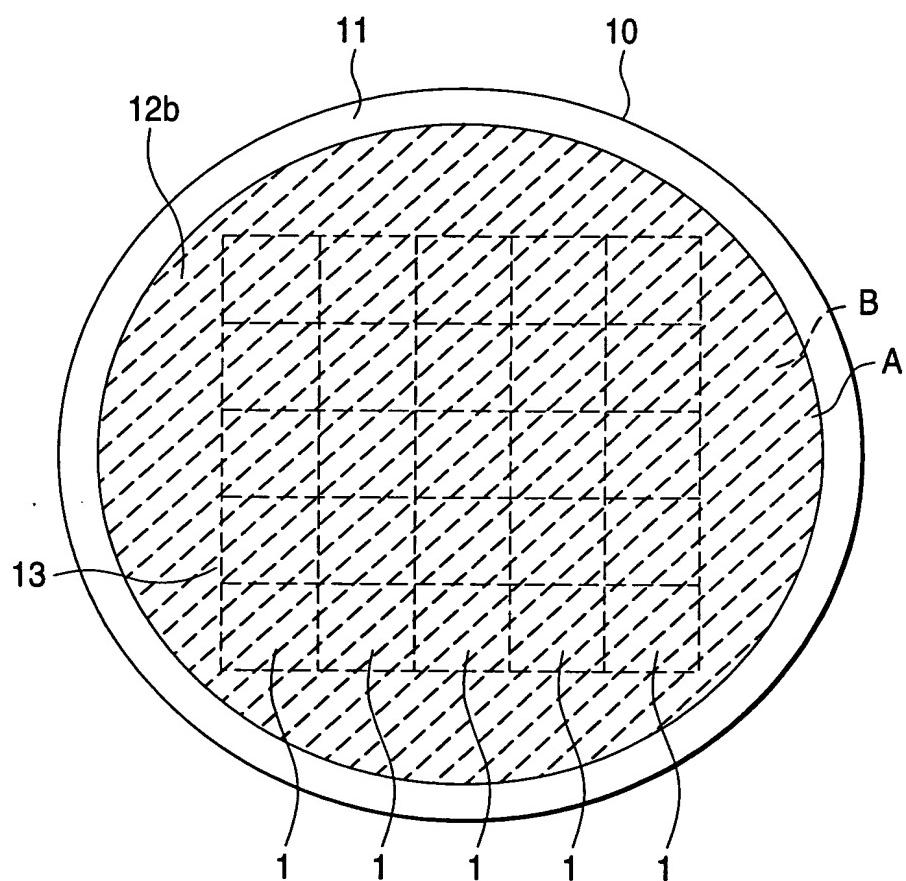
FIG. 10



09/599480

8/17

FIG. 11



69/599440

9/17

FIG. 12A

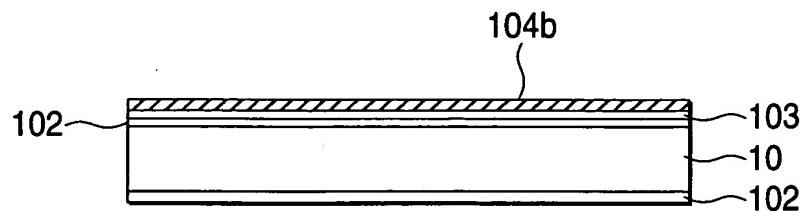


FIG. 12B

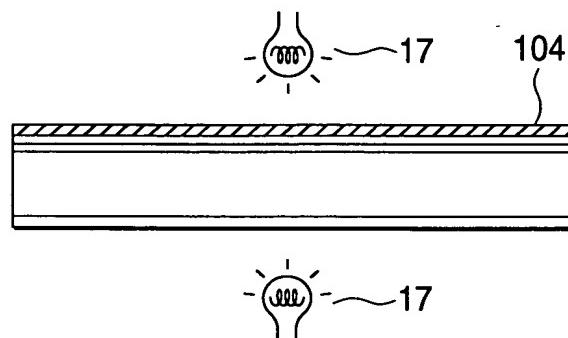


FIG. 12C

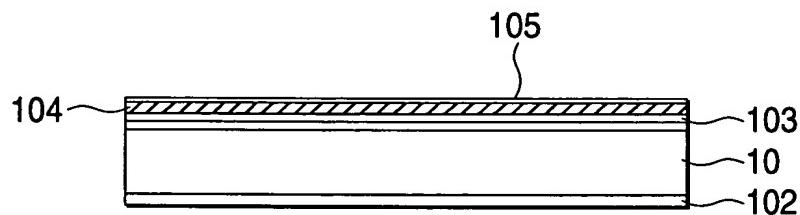


FIG. 12D

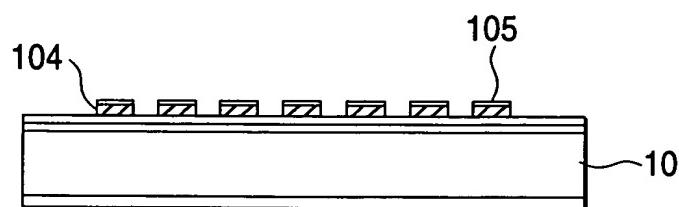
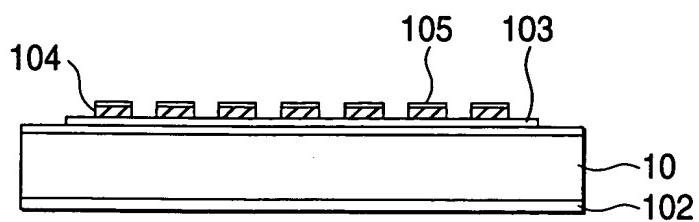


FIG. 12E



09/599444

10/17

FIG. 13F

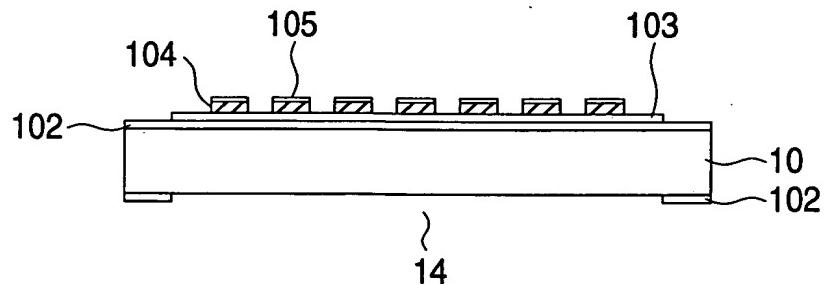


FIG. 13G

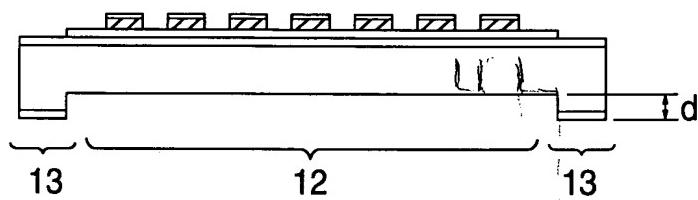


FIG. 13H

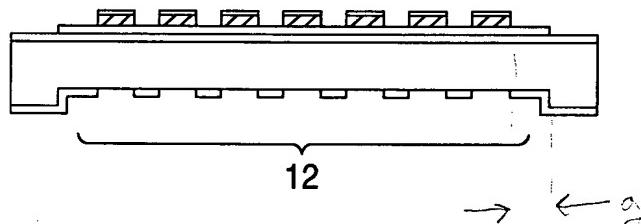


FIG. 13I

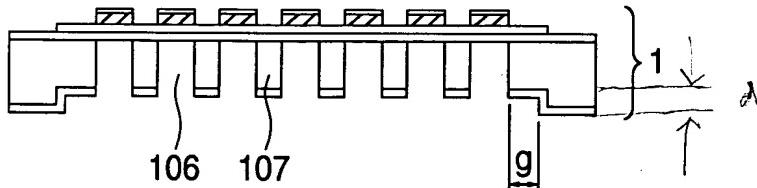
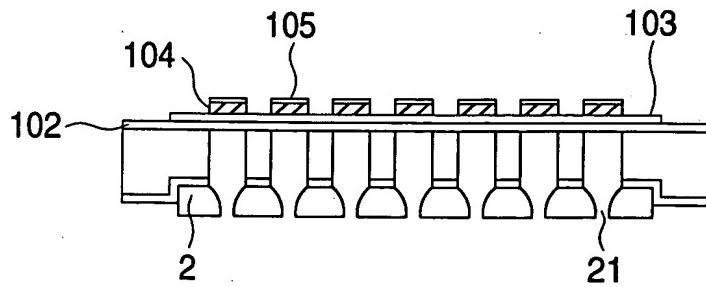


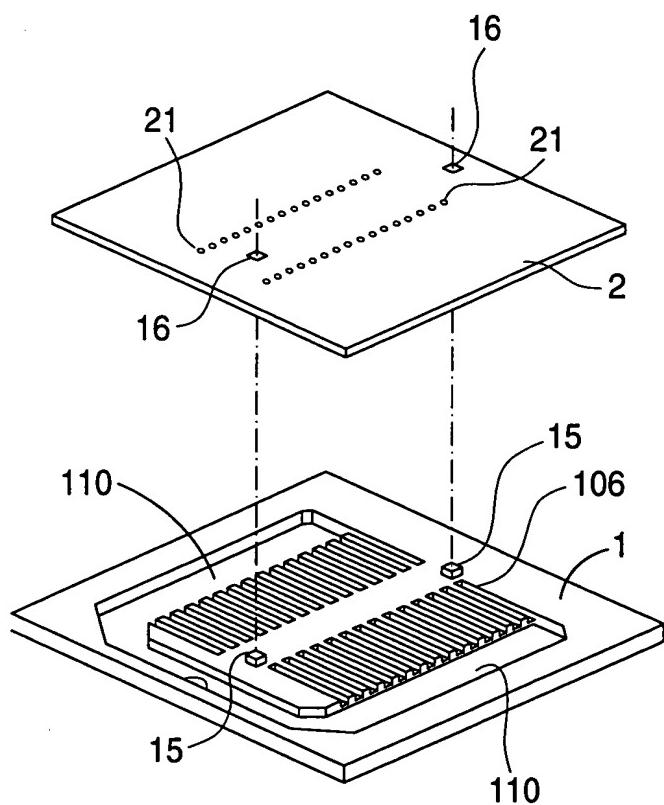
FIG. 13J



09/5798440

11/17

FIG. 14



09/599440

12/17

FIG. 15F

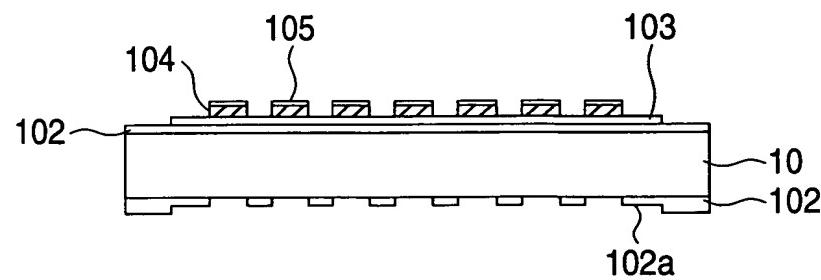


FIG. 15G

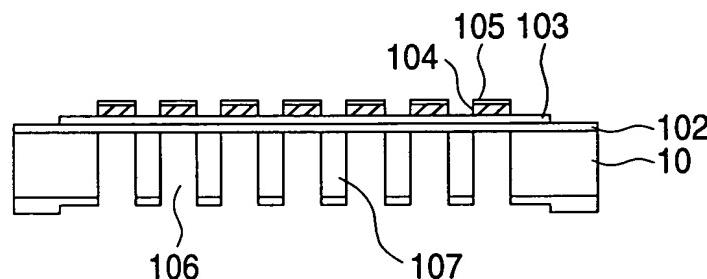


FIG. 15H

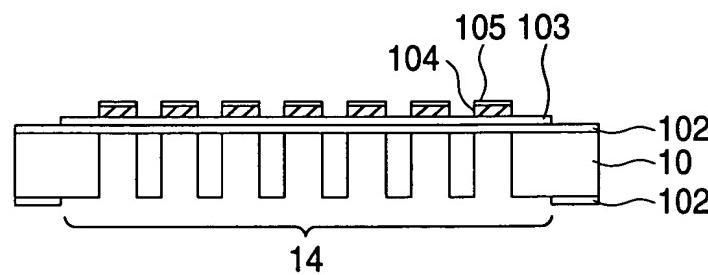
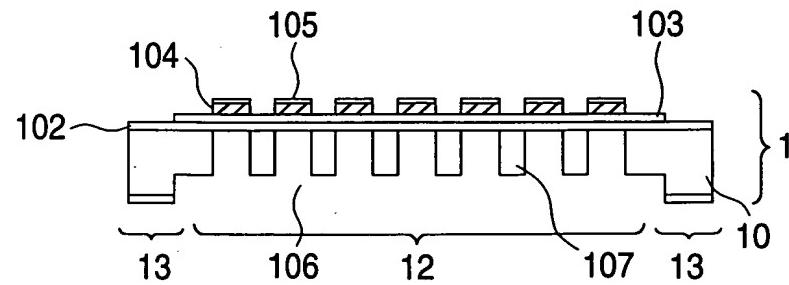


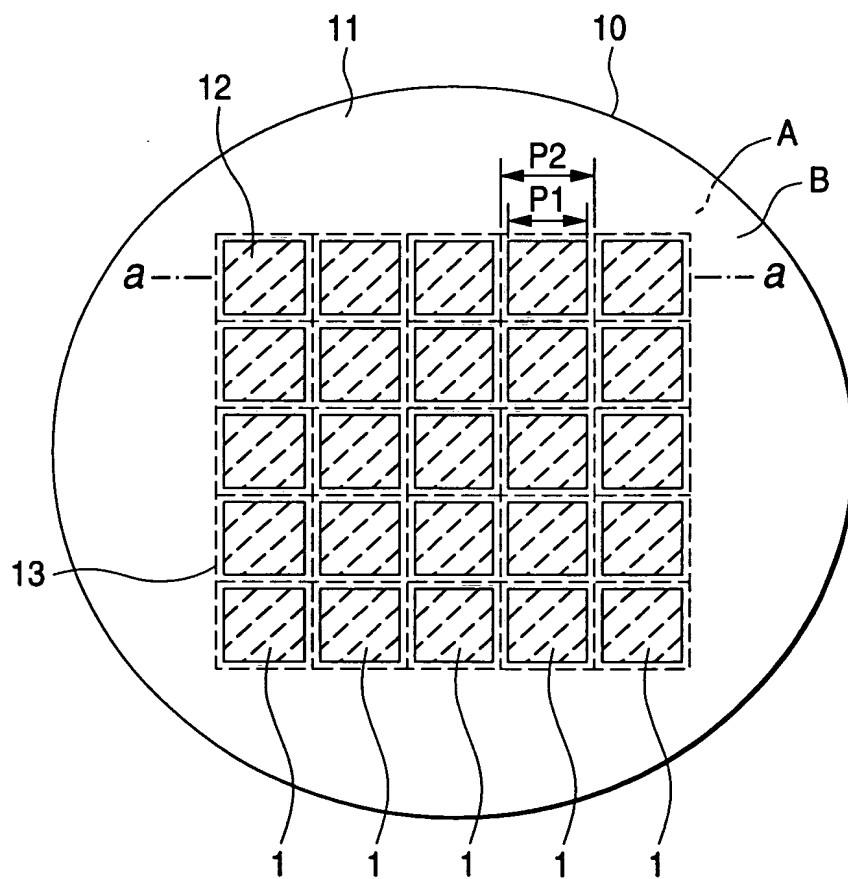
FIG. 15I



09/599940

13/17

FIG. 16



09/599446

14/17

FIG. 17A

WATER CLEANING 

FIG. 17B

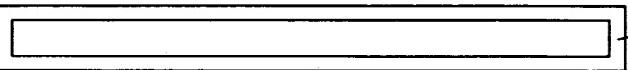
LAYER-TO-BE-PROCESSED FORMATION 

FIG. 17C

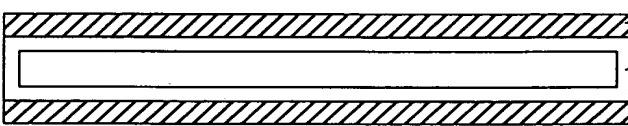
RESIST APPLICATION 

FIG. 17D

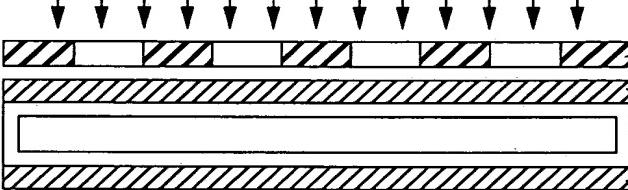
EXPOSURE 

FIG. 17E

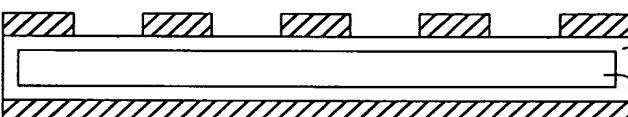
DEVELOPMENT 

FIG. 17F

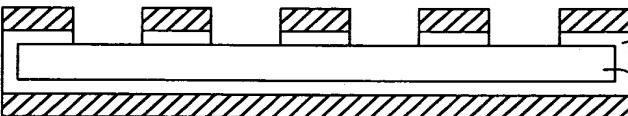
ETCHING 

FIG. 17G

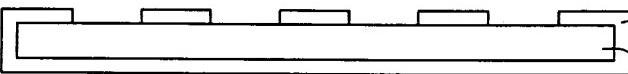
RESIST REMOVAL 

FIG. 17H

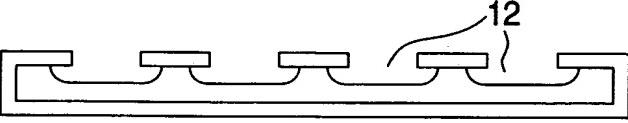
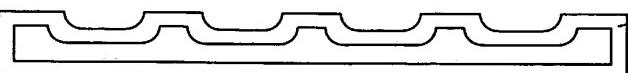
SILICON ETCHING 

FIG. 17I

THERMAL OXIDE FILM ETCHING 

FIG. 17J

FILM-TO-BE-PROCESSED FORMATION 

09/599440

15/17

FIG. 18A

OSCILLATING PLACE
FILM FORMATION

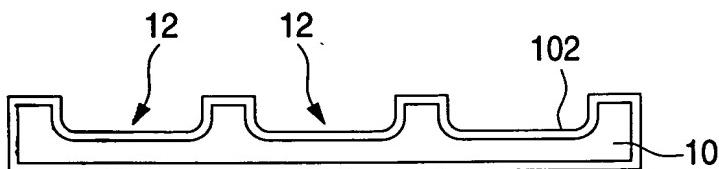


FIG. 18B

PIEZOELECTRIC
SUBSTANCE FORMATION

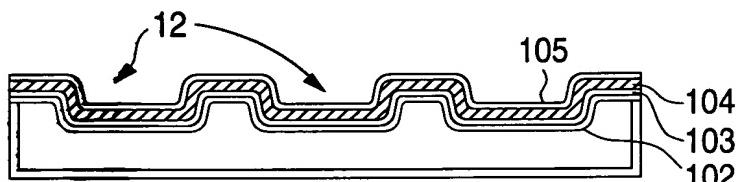


FIG. 18C

RESIST FORMATION

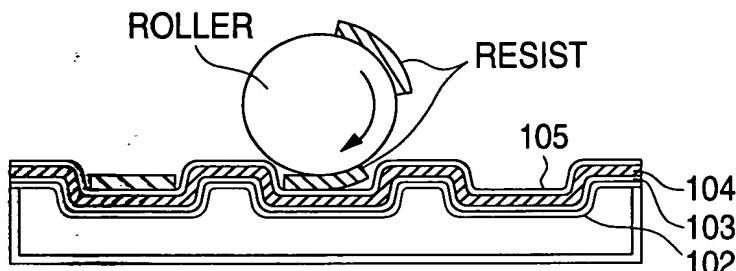


FIG. 18D

MASK EXPOSURE

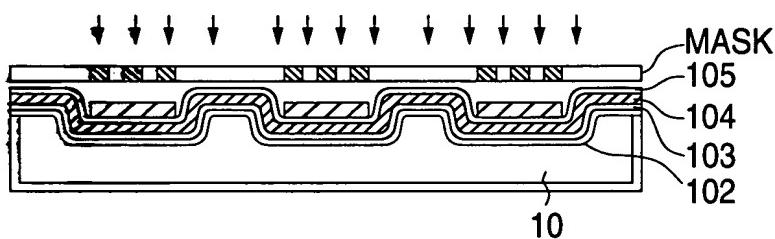


FIG. 18E

DEVELOPMENT

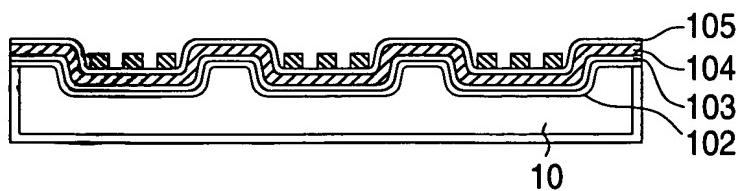
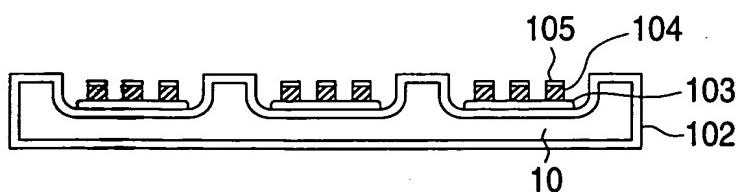


FIG. 18F

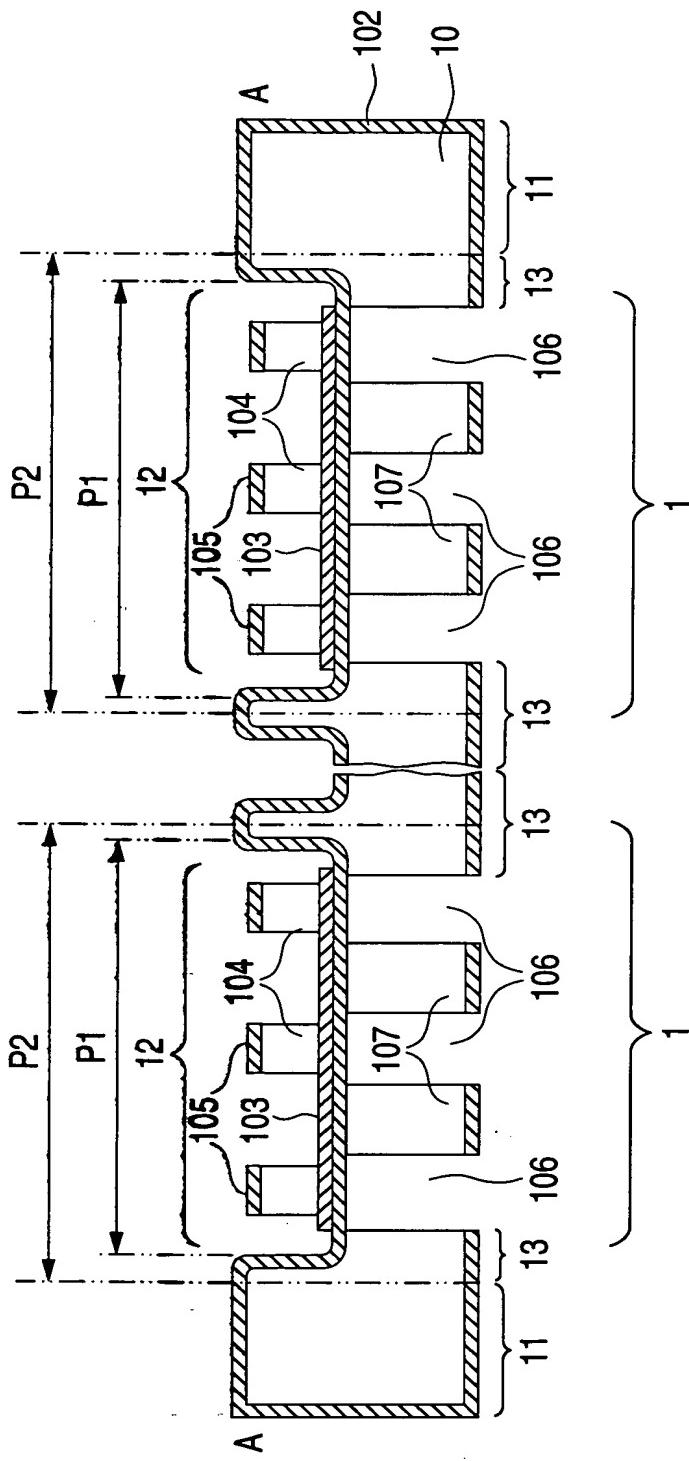
ETCHING



09/5/99448

16/17

FIG. 19



69/599448

17/17

FIG. 20

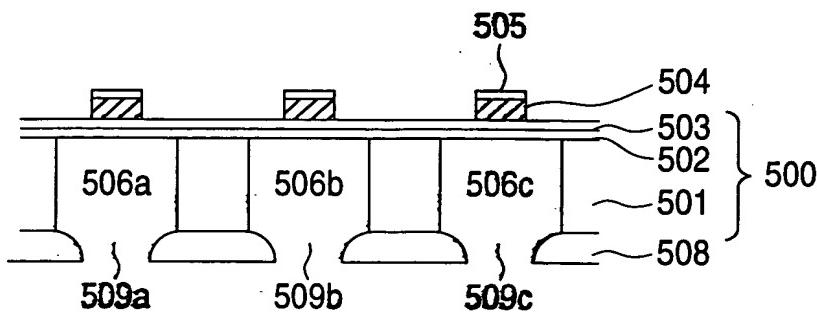


FIG. 21

